

a gate insulating film formed on the first region and containing silicon, nitrogen and oxygen;

a gate electrode formed on the gate insulating film and containing silicon; and

a post oxide film formed on the second region, containing silicon and oxygen and arranged to be in contact with the gate electrode and the gate insulating film.

2. (Amended) A semiconductor device according to claim 1, wherein a portion of the gate insulating film which is in contact with the semiconductor substrate contains nitrogen at a concentration higher than the concentration in a residual portion of the gate insulating film.

3. (Amended) A semiconductor device according to claim 2, wherein the concentration of nitrogen in a portion of the gate insulating film which is in contact with the semiconductor substrate is  $5 \times 10^{13} \text{ cm}^{-2}$  or higher.

4. (Amended) A semiconductor device according to claim 1, wherein the post oxide film further contains nitrogen, and a portion of the post oxide film which is in contact with the semiconductor substrate and the gate electrode film has a concentration higher than the concentration in the residual portion of the post oxide film.

5. (Amended) A semiconductor device according to claim 1, wherein the gate insulating film is a silicon oxide film containing nitrogen, and the gate electrode is a polycrystalline silicon film containing a dopant.

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